

TECHNICAL DATA DATA SHEET 4207, REV. -

# **Isolated Diode Array**

### **Applications:**

- High Frequency Data Lines
- RS-323 & RS-432 Networks
- LAN, Ethernet, I/O Ports
- IEC61000-4 compatible for ESD / EFT / Surge

#### Features:

- Protects up to 8 I/O Ports
- Isolated diodes eliminate crosstalk
- High Density Packaging
- High Breakdown Voltage; High Speed Switching (< 10 nsec)
- Low Capacitance; Low Leakage
- Hermetic Ceramic package
- TX, TXV, S level screening available

## **Maximum Ratings:**

All ratings are at 25 °C unless otherwise noted

Characteristics	Symbol	Condition	Max.	Units
Reverse Breakdown Voltage	$V_{BR}$	Per diode, Pulsed @ $I_R = 5 \mu A$	75	Vdc
		$P_w$ =300 μs +/- 50μs; duty $\leq$ 2%		
Continuous Forward Current	I <sub>F</sub>	Per diode, Derate at 2.4 mA/°C above 25 °C	300	mA
Peak Surge Current	I <sub>FSM</sub>	Per diode, tp=8.3 msec	500	mA
Power Dissipation	$P_{D}$	Per Junction	400	mW
Power Dissipation	$P_{D}$	Per Package, Derate at 4 mW/°C above 25 °C	500	mW
Max. Operating Temperature	TJ	-	-65 to +150	°C
Max. Storage Temperature	$T_{stg}$	-	-65 to +200	°C

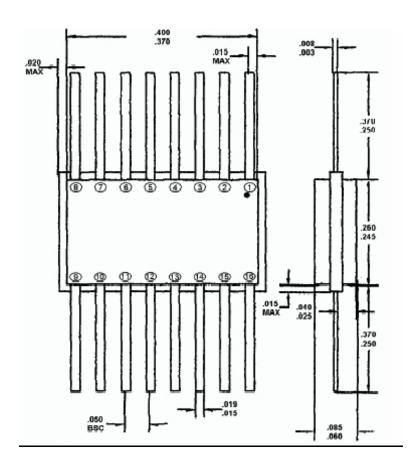
#### **Electrical Characteristics:**

All ratings are per diode and at 25 °C unless otherwise noted

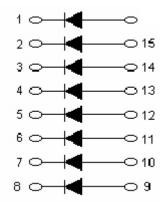
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	$V_{F1}$	$I_F$ = 100mA, Pulsed: $P_w$ =300µs +/- 50µs; duty cycle $\leq$ 2%	1.00	V
Max. Reverse Current	I <sub>R1</sub>	@V <sub>R</sub> = 40V	0.1	μΑ
	$I_{R2}$	@V <sub>R</sub> = 20V	25	nA
Max. Capacitance (Pin to Pin)	Ст	@V <sub>R</sub> = 0V, F=1MHz	4.0	pF
Max. Forward Recovery Time	$T_{FR}$	I <sub>F</sub> = 100mA	15	ns
Max. Reverse Recovery Time	T <sub>RR</sub>	$I_f = I_R = 10$ mA, $I_{RR} = 1$ mA, $I_{RL} = 100$ ohms	10	ns
Max. Forward Voltage Match	$V_{F5}$	$I_f = 10 \text{mA}$	5	mV

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### Mechanical Dimensions: in inches / mm



### **Electrical Schematic**



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